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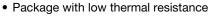
Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)}$ (Ω) at V_{GS} = -10 V	0.0067				
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.0088				
I _D (A)	-120				
Configuration	Single				

• TrenchFET® power MOSFET

FEATURES

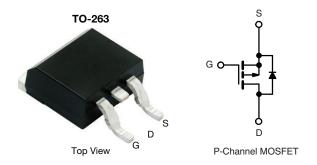




AEC-Q101 qualified ^d

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION				
Package	TO-263			
Lead (Pb)-free and Halogen-free	SQM120P06-07L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current a	T _C = 25 °C ^a	I _D	-120		
Continuous Drain Current "	T _C = 125 °C		-98		
Continuous Source Current (Diode Conduction) ^a		Is	-120	Α	
Pulsed Drain Current b		I _{DM}	-480		
Single Pulse Avalanche Current			-80		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	320	mJ	
Maximum Power Dissipation b	T _C = 25 °C		375	W	
waximum rower bissipation	T _C = 125 °C		125		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient PCB Mount ^c		R_{thJA}	40	°C/W	
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2~\%$.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	-	-			·			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	1	-	-50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	=	-	-250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-120	-	-	Α	
		V _{GS} = -10 V	I _D = -30 A	1	0.0056	0.0067		
Drain-Source On-State Resistance a	В	V _{GS} = -10 V	I _D = -30 A, T _J = 125 °C	-	-	0.0110	Ω	
Dialii-Source Oil-State nesistance	R _{DS(on)}	V _{GS} = -10 V	I _D = -30 A, T _J = 175 °C	=	-	0.0130		
		V _{GS} = -4.5 V	I _D = -20 A	=	0.0070	0.0088		
Forward Transconductance b	9fs	V _{DS} = -15 V, I _D = -30 A		-	90	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}				11 423	14 280		
Output Capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	1034	1295	pF	
Reverse Transfer Capacitance	C _{rss}			-	809	1015		
Total Gate Charge ^c	Qg			1	180	270		
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -110 \text{ A}$	-	31	-	nC	
Gate-Drain Charge ^c	Q_{gd}			-	43	-		
Gate Resistance	R _g	f = 1 MHz		1.1	2.27	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	15	23		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_L = 0.27 \Omega$ $I_D \cong -110 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		=	23	35		
Turn-Off Delay Time ^c	t _{d(off)}			-	97	146	ns	
Fall Time ^c	t _f			-	32	48		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	-480	Α	
Forward Voltage	V _{SD}	I _F = -100 A, V _{GS} = 0 V		-	-0.95	-1.5	V	
	•	1			•		•	

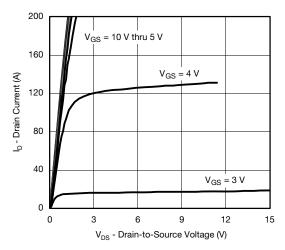
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

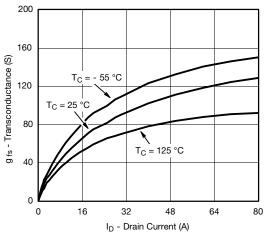
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



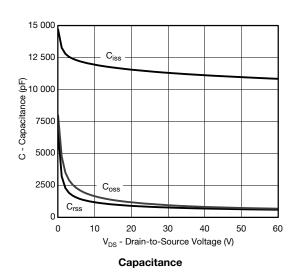
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

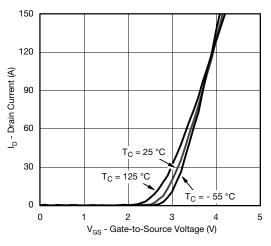


Output Characteristics

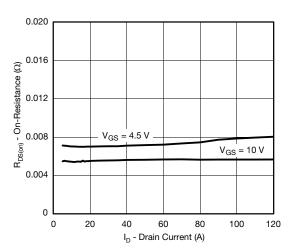


Transconductance

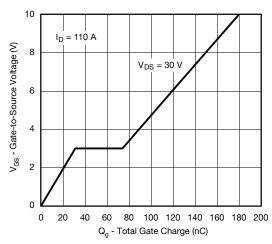




Transfer Characteristics



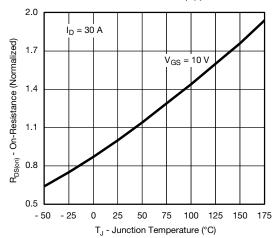
On-Resistance vs. Drain Current



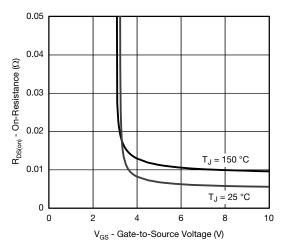
Gate Charge



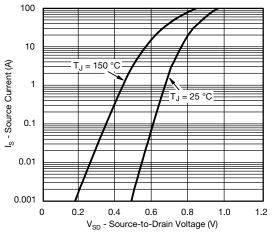
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



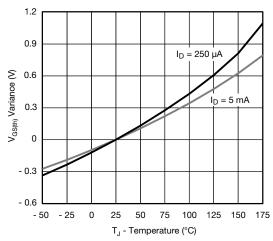
On-Resistance vs. Junction Temperature



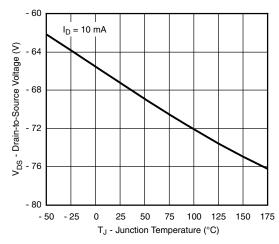
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



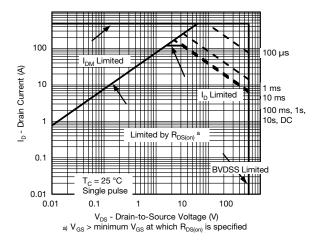
Threshold Voltage



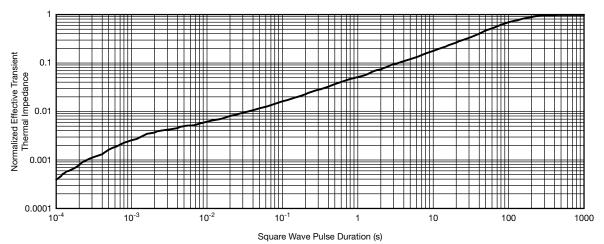
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



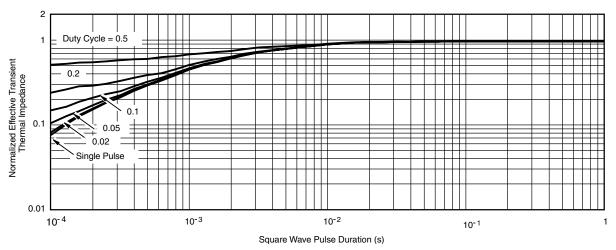
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

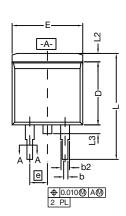
Note

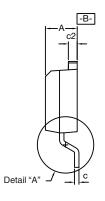
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

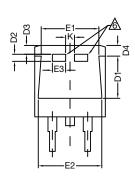
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267026.



TO-263 (D²PAK): 3-LEAD

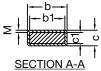








DETAIL A (ROTATED 90°)



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- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INCHES		MILLIN	METERS
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	=
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100) BSC	2.54	BSC
	K	0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
	L4	0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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